

**SMD/883B**
**AD660**
**Scope**

This specification covers the detail requirement for a complete, monolithic 16-bit digital-to-analog converter (DACPORT®) with an on-board reference, output amplifier and double buffered latches. The electrical specifications match the Standard Military Drawing (SMD) 5962-94633 in effect at the release of this data sheet. For a copy of the latest official SMD, contact DESC-ELDS.

**Part Number/Case Outline**

For case outline dimensions, see Package Information Appendix of General Specification ADI-M-1000. The complete part numbers of these SMD and 883 devices are as follows:

Device Type	SMD	ADI 883	Package Description	Package Designation	
	Part Number	Part Number		ADI	MIL-STD-1835
01	5962-9463301MLA	AD660SQ/883B	24-Pin Cerdip	Q-24	GDIP3-T24

**Absolute Maximum Ratings.**<sup>1</sup> ( $T_A = -25^\circ\text{C}$  unless otherwise noted)

$V_{LL}$ to DGND	.....	-0.3 V to +7 V
$V_{CC}$ to AGND	.....	-0.3 V to +17.0 V
$V_{EE}$ to AGND	.....	+0.3 V to -17.0 V
AGND to DGND	.....	$\pm 1$ V
Digital Inputs (Pins 5-12 and 14-19) to DGND	.....	-1.0 V to +7.0 V
REF IN to AGND	.....	$\pm 10.5$ V
Span/Bipolar Offset to AGND	.....	+10.5 V
Ref Out, $V_{OUT}$	.....	Indefinite Short to AGND, DGND, $V_{CC}$ , $V_{EE}$ , and $V_{LL}$
Power Dissipation		
To +60°C	.....	1000 mW
Derates above +60°C	.....	8.7 mW/°C
Storage Temperature	.....	-65°C to +150°C
Lead Temperature (Soldering 10 sec)	.....	+300°C

**Recommended Operating Conditions**

$V_{LL, \text{max}}$	.....	+5 V
$V_{CC}/V_{EE}$	.....	$\pm 15$ V
Ambient Temperature Range	.....	-55°C to +125°C

**Thermal Characteristics**

Thermal Resistance, Junction-to-Case ( $\theta_{JC}$ ) max	.....	28°C/W
Thermal Resistance, Junction-to-Ambient ( $\theta_{JA}$ ) max	.....	80°C/W

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**NOTE**

<sup>1</sup>Permanent damage may occur if any absolute maximum rating is exceeded. Functional operation is not implied, and device reliability may be impaired by exposure to higher-than-recommended voltages for extended periods of time.

REV. B

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# AD660—SPECIFICATIONS

Table I. Electrical Performance Characteristics

Test	Symbol	Conditions <sup>1</sup> $V_{CC} = +15\text{ V}$ , $V_{EE} = -15\text{ V}$ , $V_{LL} = +5\text{ V}$ unless otherwise specified	Group A Subgroup	Device Type	Limits		Units
					Min	Max	
Resolution <sup>2</sup>	RES		1	01	16		Bits
Relative Accuracy	RA		1	01		2	±LSB
			2, 3			4	
Differential Nonlinearity	DNL	Major Carry Errors	1	01		2	±LSB
			2, 3			4	
Gain Error <sup>3, 4</sup>	$A_E$	All Bits On	1	01		0.10	±% of FSR
Gain Drift <sup>3</sup>	$TCA_E$	All Bits On	2, 3	01		25	ppm/°C
Unipolar Offset Error	$V_{OS}$	All Bits Off	1	01		2.5	±mV
Unipolar Offset Tempo	$TCV_{OS}$	All Bits Off	2, 3	01		3	ppm/°C
Bipolar Zero Error	$B_{PZE}$	MSB On, All Others Off	1	01		7.5	±mV
Bipolar Zero Tempo	$TCB_{PZE}$	MSB On, All Others Off	2, 3	01		5	ppm/°C
Reference Output Voltage	$V_{REF}$		1	01	9.99	10.01	V
Reference Output Drift	$TCV_{REF}$		2, 3	01		25	ppm/°C
Reference Output External Current <sup>2, 5</sup>	$I_{V_{REF}}$		1	01	2		mA
Reference Output Capacitive Load <sup>2</sup>	$CLV_{REF}$		1	01		1000	pF
Reference Input Resistance <sup>2</sup>	$R_{IN}$		1	01	7	13	kΩ
Bipolar Offset Input Resistance <sup>2</sup>	$R_{IN,BPO}$		1	01	7	13	kΩ
Output Voltage Range <sup>2</sup>	$V_{OUT}$	Unipolar Range	1	01	0	+10	V
		Bipolar Range			-10	-10	
Output Current <sup>2</sup>	$I_{OUT}$		1	01	5		mA
Capacitive Load <sup>2</sup>	$C_L$		1	01		1000	pF
Output Voltage Settling Time	$t_{SL}$	20 V Step, $T_A = +25^\circ\text{C}$	1	01		13	μs
		20 V Step, $T_A = -55^\circ\text{C}, +125^\circ\text{C}$	—			10 typ	
		10 V Step, $T_A = +25^\circ\text{C}$	—			6 typ	
		10 V Step, $T_A = -55^\circ\text{C}, +125^\circ\text{C}$	—			8 typ	
		LSB Step, $T_A = -55^\circ\text{C}, +125^\circ\text{C}, +25^\circ\text{C}$	—			2.5 typ	
Digital Input High Voltage	$V_{IH}$		1, 2, 3	01	2		V
Digital Input Low Voltage	$V_{IL}$		1, 2, 3	01		0.8	V
Digital Input High Current	$I_{IH}$	$V_{IH} = +5.5\text{ V}$	1, 2, 3	01		10	±μA
Digital Input Low Current	$I_{IL}$	$V_{IL} = 0\text{ V}$	1, 2, 3	01		10	±μA
Power Supply Current	$I_{UL}$	$V_{IH} = +5.5\text{ V}$ , $V_{IL} = 0.0$	1	01		2	mA
		$V_{IH} = 2.4$ , $V_{IL} = 0.4$				7.5	
	$I_{CC}$					18	
Power Supply Rejection Ratio	PSRR	$-14.25\text{ V} < V_{CC} \leq +15.75\text{ V}$	1	01		2	±ppm/%
		$-14.25\text{ V} < V_{EE} \leq -15.75\text{ V}$				2	
		$-4.5\text{ V} < V_{LL} \leq +5.5\text{ V}$				2	
Total Harmonic Distortion + Noise	THD+N	0 dB, 990.5 Hz; Sample Rate = 96 kHz	1	01		0.009	%
		-20 dB, 990.5 Hz; Sample Rate = 96 kHz				0.056	
		-60 dB, 990.5 Hz; Sample Rate = 96 kHz				5.6	
Signal-to-Noise Ratio	SNR		1	01	83		dB

## NOTES

<sup>1</sup>For 16-bit resolution, 1 LSB = 0.0015% or FSR = 15 ppm of FSR. For 15-bit resolution, 1 LSB = 0.003% of FSR = 30 ppm of FSR. For 14-bit resolution 1 LSB = 0.006% of FSR = 60 ppm of FSR. FSR stands for Full-Scale Range and is 10 V in Unipolar Mode and 20 V in Bipolar Mode.

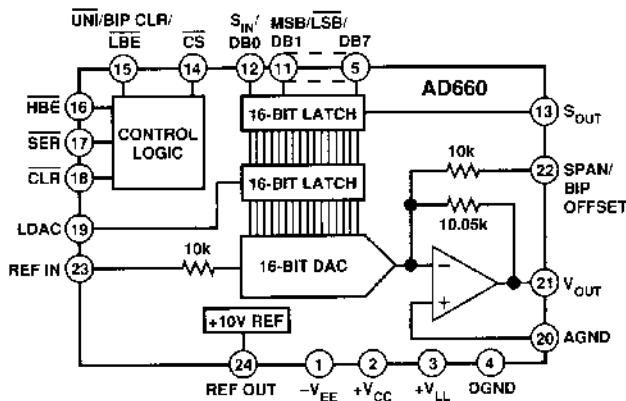
<sup>2</sup>Guaranteed, not tested parameter.

<sup>3</sup>Gain error and gain drift are measured using the internal reference.

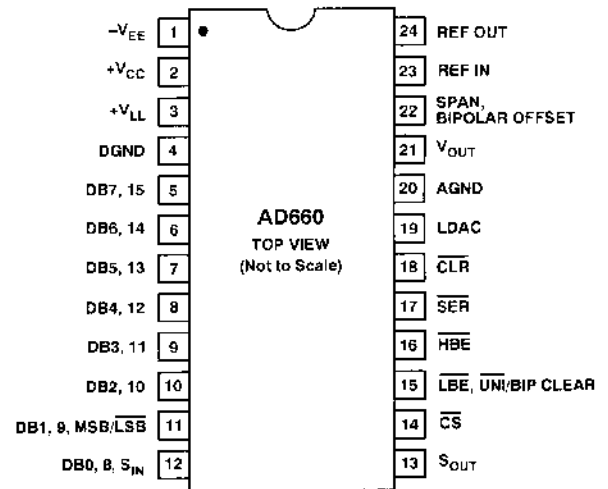
<sup>4</sup>Measured with fixed 50 Ω resistors. Eliminating these resistors increases the gain error by 0.25% of FSR (Unipolar Mode) or 0.50% of FSR (Bipolar Mode).

<sup>5</sup>External current is defined as the current available in addition to that supplied to REF IN and SPAN/BIPOLAR OFFSET.

## Functional Block Diagram and Terminal Assignments



## Q-24 Package

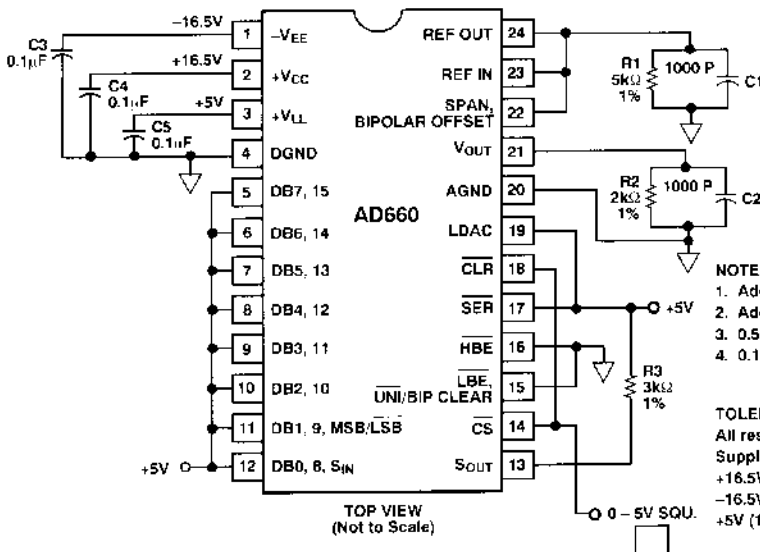


## Microcircuit Technology Group

This microcircuit is covered by technology group (56).

## Life Test/Burn-In Circuit

Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).



- NOTE:**
1. Add MR-820 diodes across supplies once per board (3 diodes).
  2. Add 47μF 35V elect caps to +/-16.5V, +5V supplies once per board.
  3. 0.5A fuse in series with 47μF cap and GND.
  4. 0.1μF caps once per supply on each socket.

**TOLERANCES**  
 All resistors 1%  
 Supply currents (per dev)  
 +16.5V (+18mA)  
 -16.5V (-15mA)  
 +5V (1mA)

# AD660

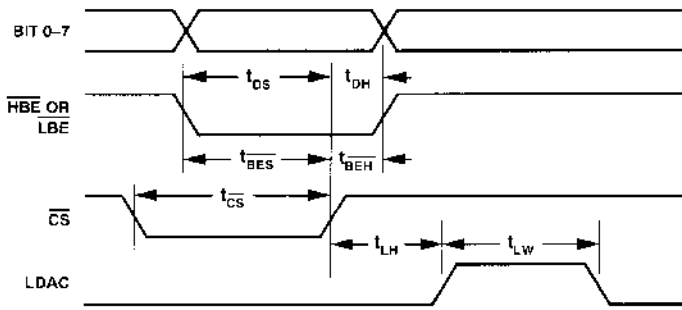


Figure 1a. AD660 Byte Load Timing

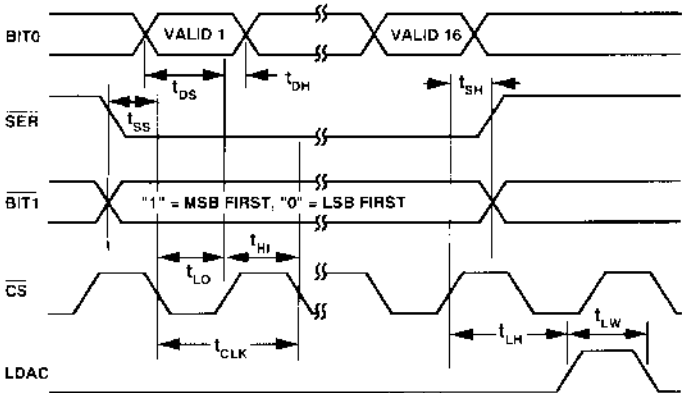


Figure 1b. AD660 Serial Load Timing

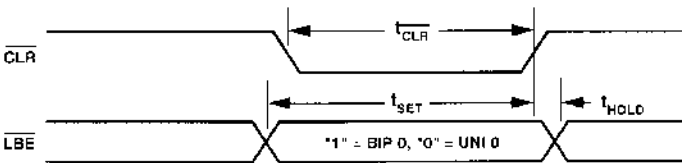


Figure 1c. Asynchronous Clear to Bipolar or Unipolar Zero

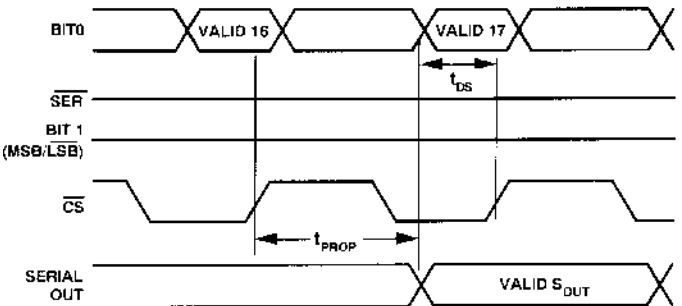


Figure 1d. Serial Out Timing

**TIMING CHARACTERISTICS**  $V_{CC} = +15 \text{ V}$ ,  
 $V_{EE} = -15 \text{ V}$ ,  $V_{LL} = +5 \text{ V}$ ,  $V_{HI} = 2.4 \text{ V}$ ,  $V_{LO} = 0.4 \text{ V}$ ,  
 timing parameters are guaranteed not tested.

Parameter	Subgroup 9	Subgroups 10, 11	Units
(Figure 1a)			
$t_{CS}$	40	50	ns min
$t_{DS}$	40	50	ns min
$t_{DH}$	0	10	ns min
$t_{BES}$	40	50	ns min
$t_{BEH}$	0	10	ns min
$t_{LH}$	80	100	ns min
$t_{LW}$	40	50	ns min
(Figure 1b)			
$t_{CLK}$	80	100	ns min
$t_{LO}$	30	50	ns min
$t_{HI}$	30	50	ns min
$t_{SS}$	0	10	ns min
$t_{DS}$	40	50	ns min
$t_{DH}$	0	10	ns min
$t_{SH}$	0	10	ns min
$t_{LH}$	80	100	ns min
$t_{LW}$	40	50	ns min
(Figure 1c)			
$t_{CLR}$	80	110	ns min
$t_{SET}$	80	110	ns min
$t_{HOLD}$	0	10	ns min
(Figure 1d)			
$t_{PROP}$	50	100	ns min
$t_{DS}$	50	80	ns min

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